

## N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A) <sup>a, e</sup>	Q <sub>g</sub> (Typ)
30	0.0012 at V <sub>GS</sub> = 10 V	300	72 nC
	0.0017 at V <sub>GS</sub> = 4.5 V	210	

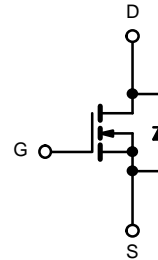
### FEATURES

- DT-Trench Power MOSFET
- 100 % R<sub>g</sub> and UIS Tested
- Compliant to RoHS Directive 2011/65/EU



### APPLICATIONS

- OR-ing
- Server
- DC/DC



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C, unless otherwise noted)				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V <sub>DS</sub>	30	V	
Gate-Source Voltage	V <sub>GS</sub>	± 20		
Continuous Drain Current (T <sub>J</sub> = 175 °C)	I <sub>D</sub>	T <sub>C</sub> = 25 °C	300 <sup>a, e</sup>	
		T <sub>C</sub> = 70 °C	220 <sup>e</sup>	
		T <sub>A</sub> = 25 °C	115 <sup>b, c</sup>	
		T <sub>A</sub> = 70 °C	89 <sup>b, c</sup>	
Pulsed Drain Current	I <sub>DM</sub>	850	mJ	
Avalanche Current Pulse	I <sub>AS</sub>	90		
Single Pulse Avalanche Energy				
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	90 <sup>a, e</sup>	
		T <sub>A</sub> = 25 °C	3.13 <sup>b, c</sup>	
Maximum Power Dissipation	P <sub>D</sub>	T <sub>C</sub> = 25 °C	302 <sup>a</sup>	
		T <sub>C</sub> = 70 °C	184	
		T <sub>A</sub> = 25 °C	10.2 <sup>b, c</sup>	
		T <sub>A</sub> = 70 °C	5.9 <sup>b, c</sup>	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typ.	Max.	Unit	
Maximum Junction-to-Ambient <sup>b, d</sup>	R <sub>thJA</sub>	8	13	°C/W	
Maximum Junction-to-Case	R <sub>thJC</sub>	0.38	0.45		

Notes:

- Based on T<sub>C</sub> = 25 °C.
- Surface mounted on 1" x 1" FR4 board.
- t = 10 sec.
- Maximum under steady state conditions is 90 °C/W.
- Calculated based on maximum junction temperature. Package limitation current is 90 A.

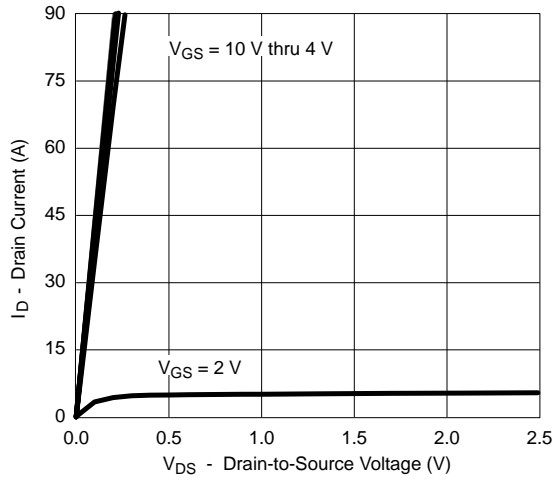
<b>SPECIFICATIONS</b> ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	30			V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$		35		mV/ $^\circ\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			-7.5		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1.0		2.5	V
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 24\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 24\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			10	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	300			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 40\text{ A}$		0.0012	0.00135	$\Omega$
		$V_{GS} = 4.5\text{ V}, I_D = 40\text{ A}$		0.0017	0.0019	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}, I_D = 40\text{ A}$		110		S
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		6998		pF
Output Capacitance	$C_{oss}$			1901		
Reverse Transfer Capacitance	$C_{rss}$			910		
Total Gate Charge	$Q_g$	$V_{DS} = 15\text{ V}, V_{GS} = 10\text{ V}, I_D = 40\text{ A}$		72	87	nC
		$V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 40\text{ A}$		41	56	
$Q_{gs}$			22			
$Q_{gd}$			9			
Gate Resistance	$R_g$	$f = 1\text{ MHz}$		1.2	1.8	$\Omega$
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 0.625\text{ }\Omega$ $I_D \cong 30\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		15		ns
Rise Time	$t_r$			16		
Turn-Off Delay Time	$t_{d(off)}$			77		
Fall Time	$t_f$			13		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 0.67\text{ }\Omega$ $I_D \cong 30\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\text{ }\Omega$		25		
Rise Time	$t_r$			180		
Turn-Off Delay Time	$t_{d(off)}$			55		
Fall Time	$t_f$			12		
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25\text{ }^\circ\text{C}$			300	A
Pulse Diode Forward Current <sup>a</sup>	$I_{SM}$				850	
Body Diode Voltage	$V_{SD}$	$I_S = 22\text{ A}$		0.5	1.1	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = 20\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		25		ns
Body Diode Reverse Recovery Charge	$Q_{rr}$			86		nC
Reverse Recovery Fall Time	$t_a$			27		ns
Reverse Recovery Rise Time	$t_b$			15		

Notes:

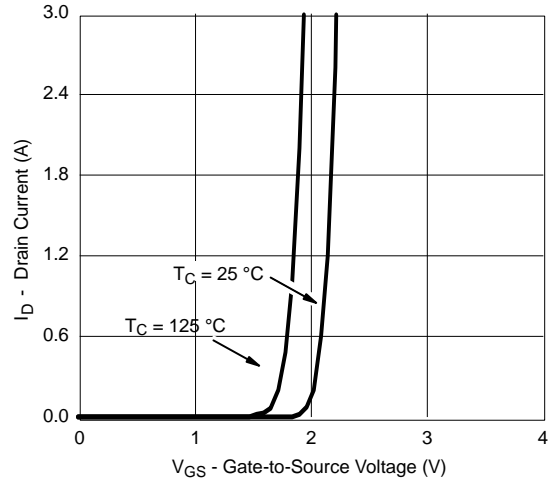
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
 b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

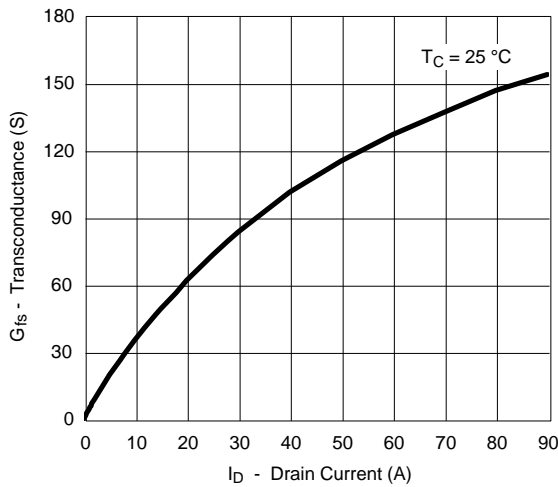
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



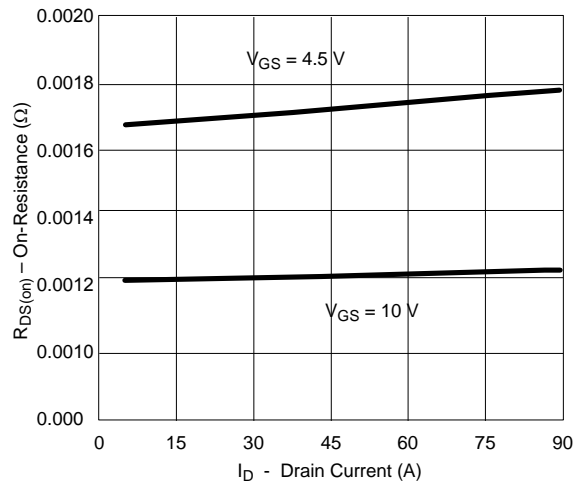
**Output Characteristics**



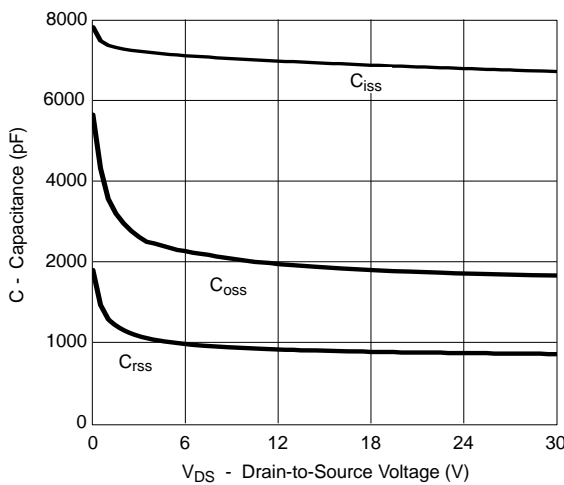
**Transfer Characteristics**



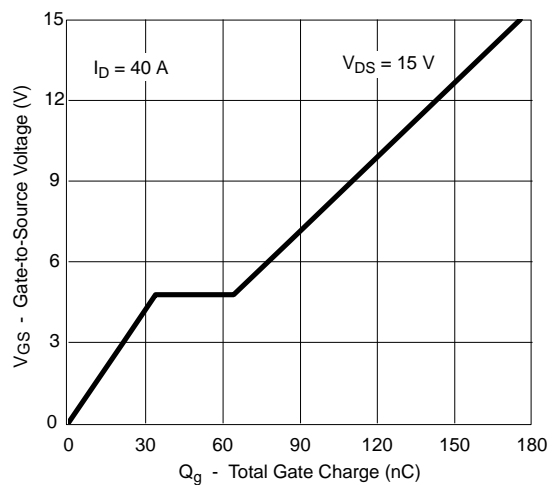
**Transconductance**



**R<sub>DS(on)</sub> vs. Drain Current**

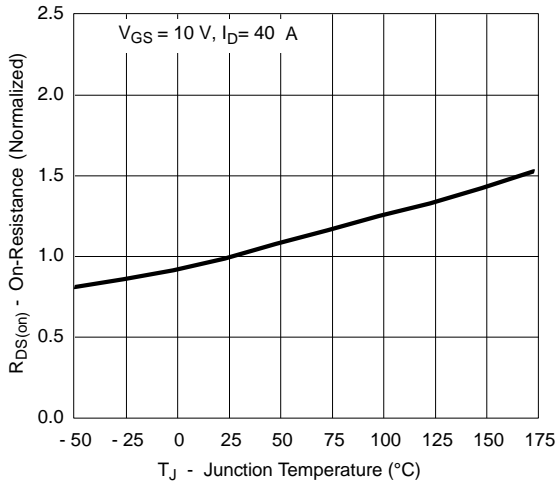


**Capacitance**

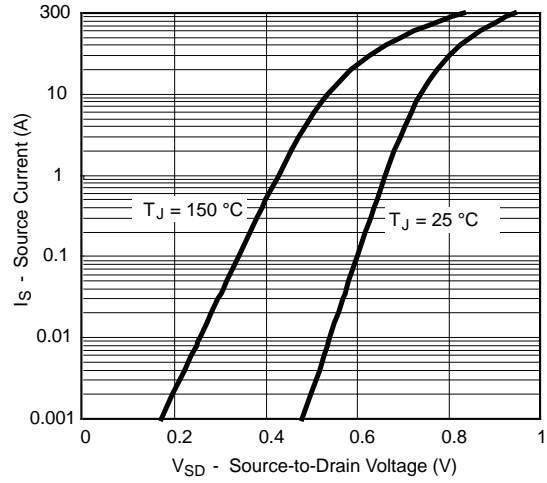


**Gate Charge**

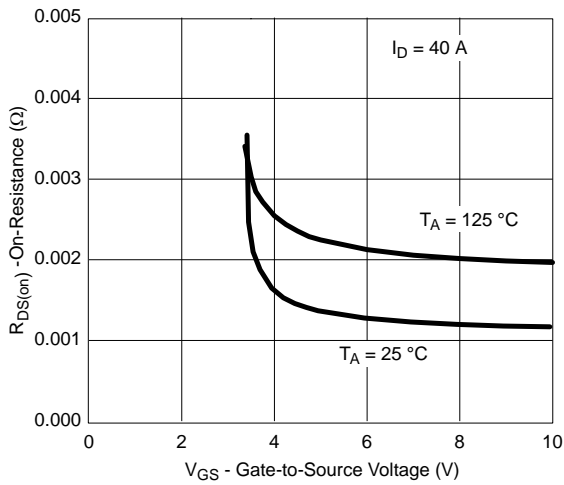
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



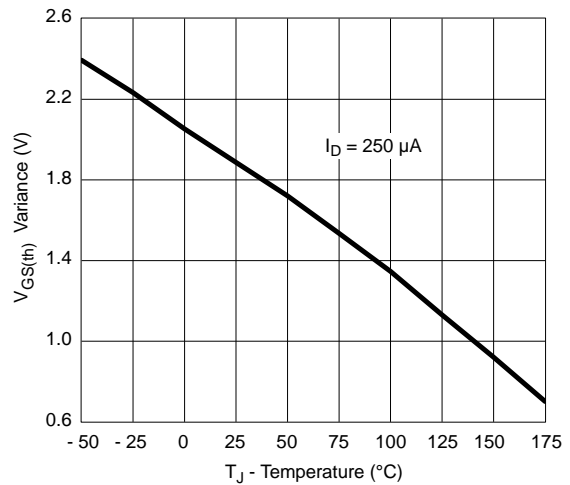
**On-Resistance vs. Junction Temperature**



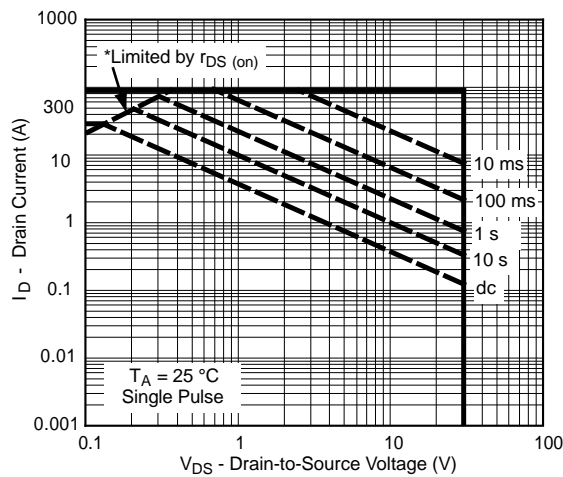
**Forward Diode Voltage vs. Temperature**



**R<sub>DS(on)</sub> vs. V<sub>GS</sub> vs. Temperature**

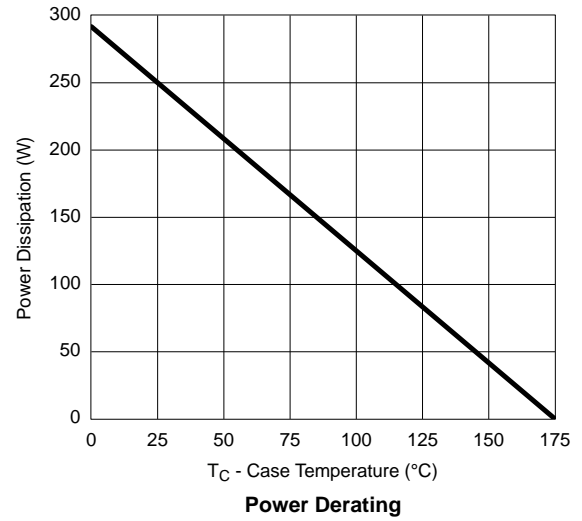
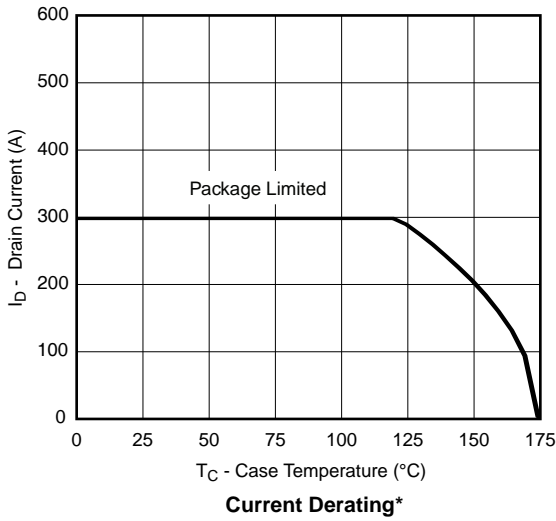


**Threshold Voltage**



**Safe Operating Area, Junction-to-Ambient**  
\* $V_{GS} >$  minimum  $V_{GS}$  at which  $r_{DS(on)}$  is specified

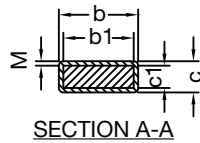
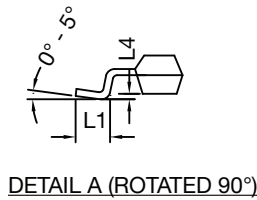
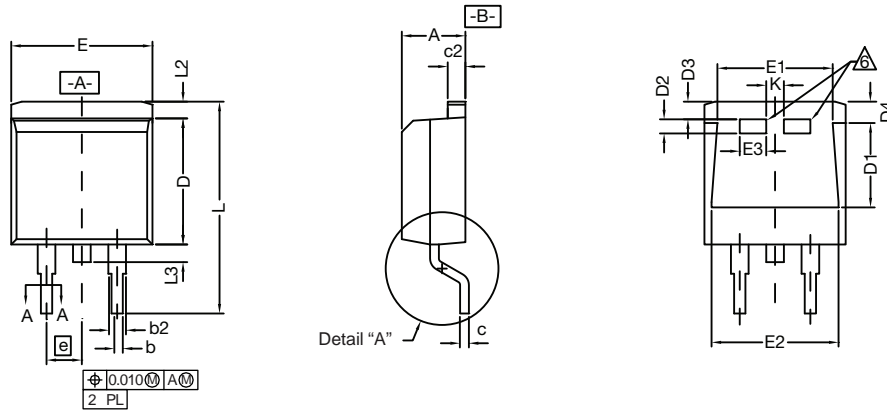
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



\*The power dissipation  $P_D$  is based on  $T_{J(max)} = 175$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



## TO-263 (D<sup>2</sup>PAK): 3-LEAD

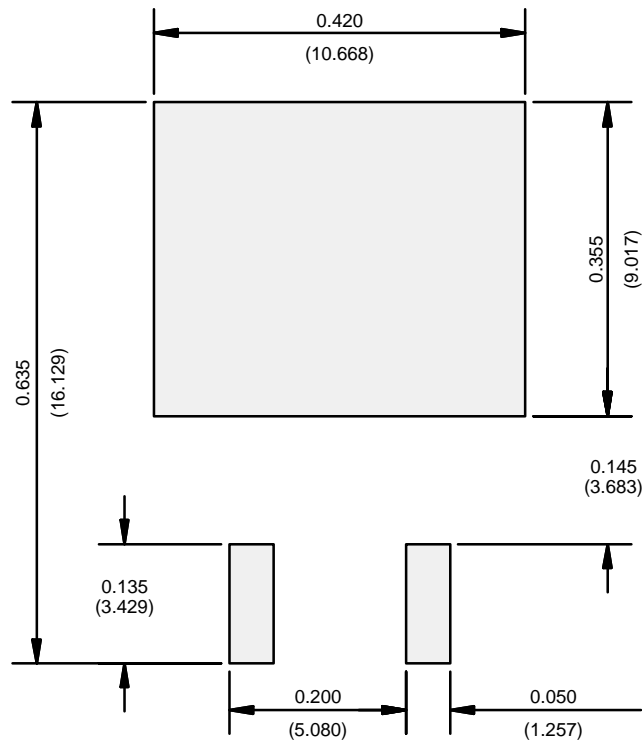


DIM.	INCHES		MILLIMETERS		
	MIN.	MAX.	MIN.	MAX.	
A	0.160	0.190	4.064	4.826	
b	0.020	0.039	0.508	0.990	
b1	0.020	0.035	0.508	0.889	
b2	0.045	0.055	1.143	1.397	
c*	Thin lead	0.013	0.018	0.330	0.457
	Thick lead	0.023	0.028	0.584	0.711
c1	Thin lead	0.013	0.017	0.330	0.431
	Thick lead	0.023	0.027	0.584	0.685
c2	0.045	0.055	1.143	1.397	
D	0.340	0.380	8.636	9.652	
D1	0.220	0.240	5.588	6.096	
D2	0.038	0.042	0.965	1.067	
D3	0.045	0.055	1.143	1.397	
D4	0.044	0.052	1.118	1.321	
E	0.380	0.410	9.652	10.414	
E1	0.245	-	6.223	-	
E2	0.355	0.375	9.017	9.525	
<b>E3</b>	0.072	0.078	1.829	1.981	
e	0.100 BSC		2.54 BSC		
K	0.045	0.055	1.143	1.397	
L	0.575	0.625	14.605	15.875	
L1	0.090	0.110	2.286	2.794	
L2	0.040	0.055	1.016	1.397	
L3	0.050	0.070	1.270	1.778	
L4	0.010 BSC		0.254 BSC		
M	-	0.002	-	0.050	
ECN: T13-0707-Rev. K, 30-Sep-13					
DWG: 5843					

**Notes**

1. Plane B includes maximum features of heat sink tab and plastic.
2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
3. Pin-to-pin coplanarity max. 4 mils.
4. \*: Thin lead is for SUB, SYB.  
Thick lead is for SUM, SYM, SQM.
5. Use inches as the primary measurement.
6. This feature is for thick lead.

**RECOMMENDED MINIMUM PADS FOR D<sup>2</sup>PAK: 3-Lead**



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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